A METHOD TO FABRICATE A SQUARE WORD LINE POLY SPACER

ABSTRACT

A new method is provided for the etch of polysilicon spacers that form part of split-gate flash memory devices. Under a first embodiment of the invention, a conventional polysilicon gate etch is augmented with an oxide based plasma treatment of the layer of polysilicon that is being etched as part of this etch. Under a second embodiment of the invention, a conventional five step etch procedure is replaced with a three step etch procedure that is based on SiON or SiN hardmask technology

Fig. 4



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